Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

T_j=25℃

Parameter	Test Conditions	Symbol	Value	Unit
DC Reverse voltage		V_R	35	V
Average rectified current		I_O	100	mA
Power dissipation		P_d	150	MW
Junction temperature		T_j	150	℃
Storage temperature range		T_{stg}	-55…+150	℃

Maximum Thermal Resistance

T_j=25℃

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=4mm, T_L=constant	R_{thJA}	350	K/W

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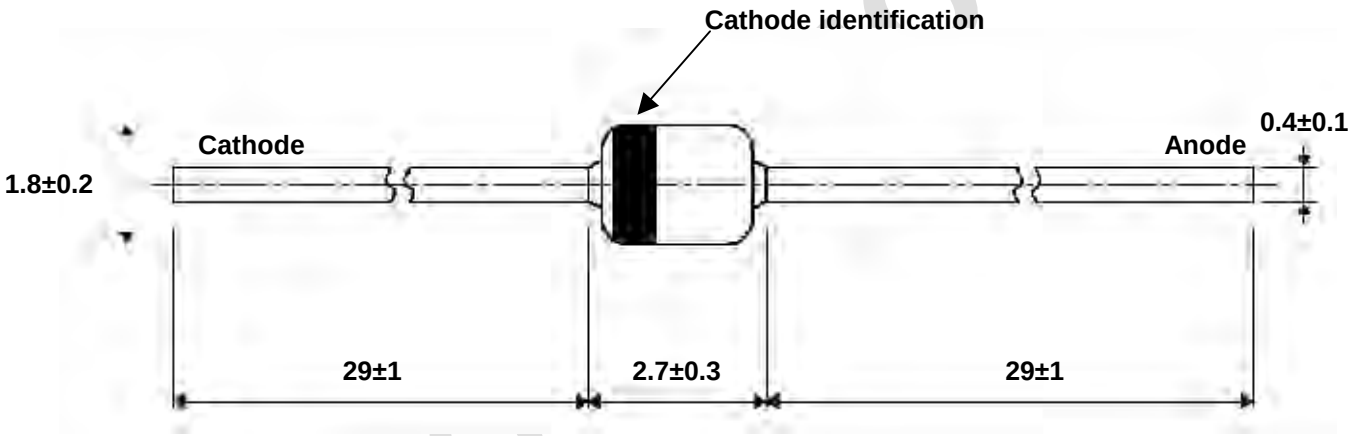
Electrical Characteristics

T_j=25℃

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=10mA	V_F		0.85	1	V
Reverse current	V_R=20V	I_R			100	nA
Breakdown voltage	I_R=10μA	B_V	35			V
Terminal capacitance	f=1MH$_Z$, V_R=6V	C_t			1.5	pF
Frequency resistance	f=100MH$_Z$, I_F=10mA	r_f			0.6	

Dimensions in mm



Standard Glass Case
JEDEC DO 34

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